



ZXTP19100CG

100V PNP MEDIUM POWER TRANSISTOR IN SOT223

Features

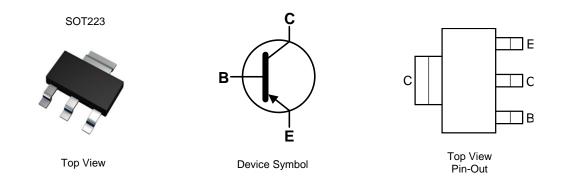
- BV_{CEO} > -100V
- $BV_{ECO} > -7V$
- I_C = -2A High Continuous Current
- Low Saturation Voltage V_{CE(sat)} < -130mV @ -1A
- $R_{CE(sat)} = 100 m\Omega$
- Complementary NPN Type: ZXTN19100CG
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.112 grams (Approximate)

Applications

- Motor Drive
- High Side Driver



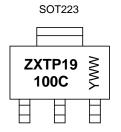
Ordering Information (Note 4)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP19100CGTA	AEC-Q101	ZXTP19100C	7	12	1,000
Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.					

. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied. 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds. 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



ZXTP19100C = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week Code (01~53)



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-110	V
Collector-Emitter Voltage (forward blocking)	V _{CEX}	-110	V
Collector-Emitter Voltage	V _{CEO}	-100	V
Emitter-Collector Voltage (reverse blocking)	V _{ECO}	-7	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	lc	-2	A
Base Current	I _B	-1	A
Peak Pulse Current	I _{CM}	-3	А

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
	(Note 5)		1.2 9.6	
Power Dissipation	(Note 6)		1.6 12.8	W
Linear Derating Factor	(Note 7)	P _D	3 24	mW/°C
	(Note 8)		5.3 42	
	(Note 5)		104	
Thermal Desistance Junction to Ambient	(Note 6)		78	
Thermal Resistance, Junction to Ambient	(Note 7)	R _{0JA}	42	°C/W
	(Note 8)		23.5	
Thermal Resistance, Junction to Lead (Note 9)		R _{θJL}	16	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

ESD Ratings (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	ЗA
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes: 5. For a device mounted with the collector lead on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.

6. Same as Note 6, except the device is mounted on 25mm x 25mm 1oz copper.

7. Same as Note 6, except the device is mounted on 50mm x 50mm 2oz copper.

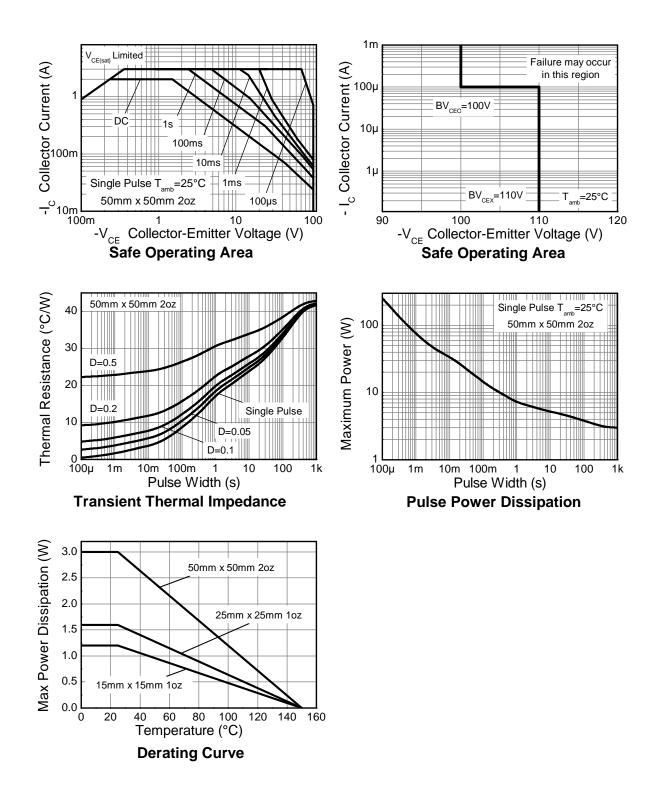
8. Same as Note 8 measured at t<5 seconds.

9. Thermal resistance from junction to solder-point (at the end of the collector lead).

10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information (@T_A = +25°C, unless otherwise specified.)





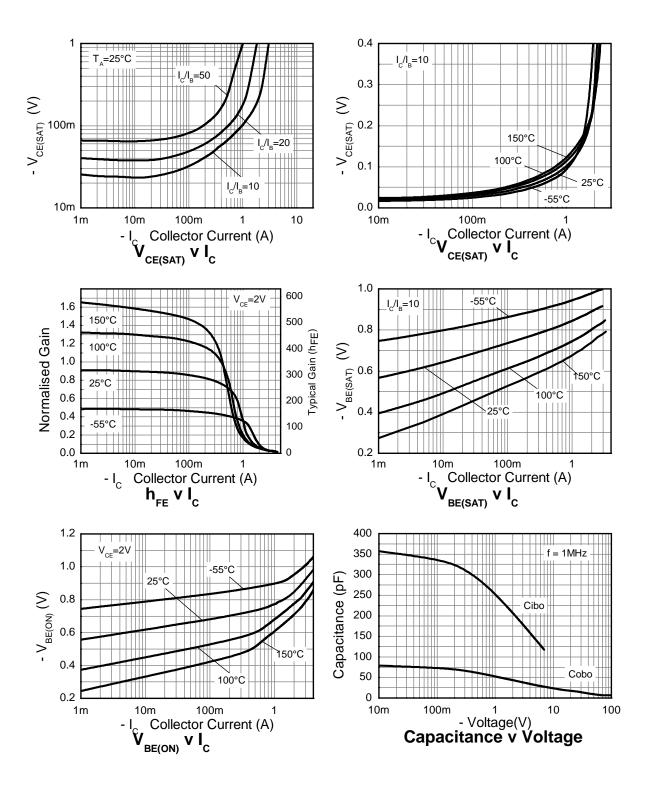
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Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-110	-135	-	V	$I_{\rm C} = -100 \mu {\rm A}$
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	-100	-135	-	V	$I_{\rm C}$ = -10mA
Collector-Base Breakdown Voltage (forward blocking)	BV _{CEX}	-110	-130			I _C = -100μA
Emitter-Collector Breakdown Voltage (reverse blocking)	BV _{ECX}	-7	-8.3	-	V	$I_{C} = -100\mu A$, $R_{BC} < 1k\Omega$ or 0.25V< $V_{BC} > -0.25V$
Emitter-Collector Breakdown Voltage (reverse blocking)	BV _{ECO}	-7	-8.7	-	V	I _E = -100μA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8.3	-	V	I _E = -100μA
Collector Cut-Off Current	I	-	< 1	-50	nA	V _{CB} = -110V
Collector Cut-On Current	I _{CBO}	-	-	-0.5	μA	V _{CB} = -110V, T _A = +100°C
Emitter Cut-Off Current	I _{EBO}	-	< 1	-50	nA	V _{EB} = -5.6V
		-	-100	-130	mV	I _C = -500mA, I _B = -20mA
Collector-Emitter Saturation Voltage (Note 11)	M	-	-100	-125	mV	$I_{\rm C} = -1A, I_{\rm B} = -100 {\rm mA}$
	V _{CE(sat)}	-	-180	-230	mV	I _C = -1A, I _B = -50mA
		-	-220	-295	mV	$I_{\rm C} = -2A, I_{\rm B} = -200 {\rm mA}$
Base-Emitter Saturation Voltage (Note 11)	V _{BE(sat)}	-	-890	-1,000	mV	$I_{\rm C} = -2A, I_{\rm B} = -200 {\rm mA}$
Base-Emitter Turn-On Voltage (Note 11)	V _{BE(on)}	-	-840	-950	mV	$I_{C} = -2A, V_{CE} = -2V$
	h _{FE}	200	300	500	-	I _C = -100mA, V _{CE} = -2V
DC Current Gain (Note 11)		70	130	-	-	$I_{C} = -1A, V_{CE} = -2V$
		20	28	-	-	$I_{C} = -2A, V_{CE} = -2V$
Current Gain-Bandwidth Product (Note 11)	fT	-	142	-	MHz	$V_{CE} = -10V, I_{C} = -100mA, f = 50MHz$
Input Capacitance (Note 11)	Cibo	-	291	400	pF	V _{EB} = -0.5V, f = 1MHz
Output Capacitance (Note 11)	C _{obo}	-	23.5	40	рF	$V_{CB} = -10V, f = 1MHz$
Delay Time	t _d	-	24.7	-	ns	
Rise Time	tr	-	22.4	-	ns	$I_{C} = -500 \text{mA}, V_{CC} = -10 \text{V},$
Storage Time	ts	-	660	-	ns	$I_{B1} = -I_{B2} = -50 \text{mA}$
Fall Time	t _f	-	107	-	ns	$R_{b} = 100W, R_{c} = 20W$

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Note: 11. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



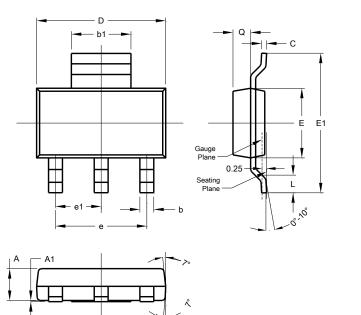
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)





Package Outline Dimensions

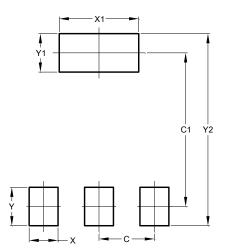
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
с	0.20	0.30	0.25		
D	6.45	6.55	6.50		
ш	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
e	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



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